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New
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster
Serial No. TO BE ASSIGNED

Filed January 3, 2002

For SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE
CRYSTAL SILICON

January 3, 2002

PRELIMINARY AMENDMENT A

TO THE COMMISSIONER OF PATENTS AND TRADEMARKS,

SIR:

Please amend the application as follows:

In the Title:

Please change the title on page 1 to the following:

SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY
DEVICE LAYER AND A PROCESS FOR THE PREPARATION THEREOF.

In the Specification:

Please replace the paragraph beginning on page 1, line 3
with the following rewritten paragraph:

CROSS-REFERENCE TO RELATED APPLICATION

This application claims priority from U.S. provisional
application Serial No. 60/098,902, filed on September 2, 1998,
U.S. application Serial Number 09/387,288 filed on August 31,